

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	$2\Omega@10V$	100mA
	$2.5\Omega@4.5V$	



合肥矽普半导体

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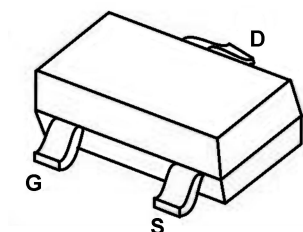
Feature

- High power and current handling capability
- Surface mount package
- ESD protected 2KV

Application

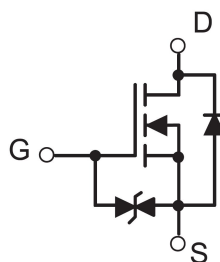
- Battery Switch
- DC/DC Converter

Package

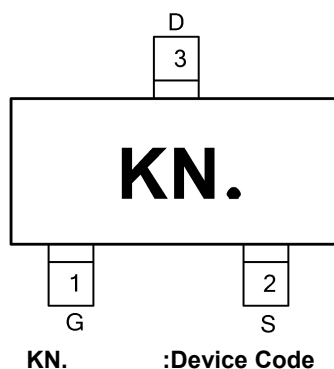


SOT-523

Circuit diagram



Marking



Order Information

Device	Package	Unit/Tape
2SK3019A	SOT-523	3000

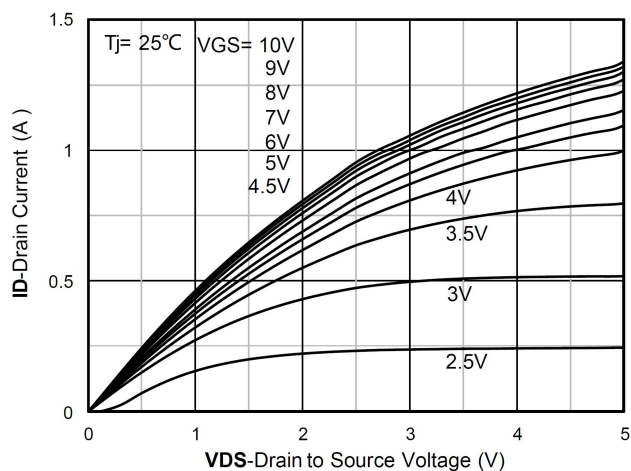
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	100	mA
Pulse Drain Current Tested	I_{DM}	400	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

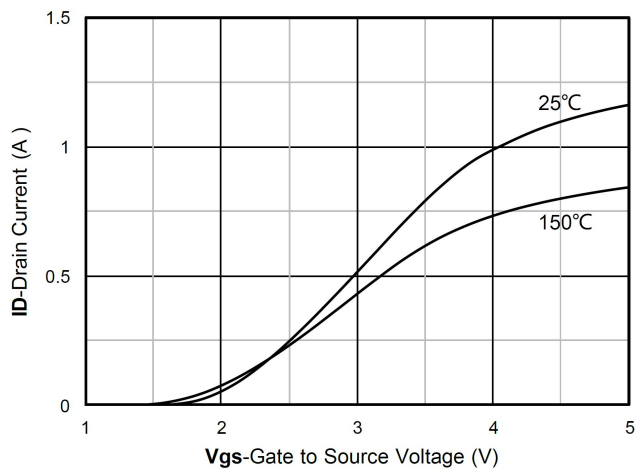
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=250μA	60	-	-	V
Drain-Source Leakage Current	IDSS	VDS=48V , VGS=0V	-	-	1	uA
Gate-Source Leakage Current	IGSS	VGS=±20V , VDS=0V	-	-	±10	uA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=250μA	0.7	1	1.45	V
Static Drain-Source On-Resistance	RDS(on)	VGS =10V, ID =200mA	-	2	5	Ω
		VGS =4.5V, ID =100mA	-	2.5	8	
Dynamic characteristics						
Input Capacitance	Ciss	VDS=25V , VGS=0V , f=1MHz	-	12	-	pF
Output Capacitance	Coss		-	6	-	
Reverse Transfer Capacitance	Crss		-	2.5	-	
Total Gate Charge	Qg	VDS=10V , VGS=15V , ID=1A	-	1.34	-	nC
Gate-Source Charge	Qgs		-	0.29	-	
Gate-Drain Charge	Qgd		-	0.2	-	
Switching Characteristics						
Turn-On Delay Time	td(on)	VDD=15V VGS=10V , RG=2.3Ω , ID=1A	-	5	-	nS
Turn-On Rise Time	tr		-	18	-	
Turn-Off Delay Time	td(off)		-	8	-	
Turn-Off Fall Time	tr		-	14	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	VSD	VGS=0V , IS=1A , TJ=25℃	-	-	1.2	V

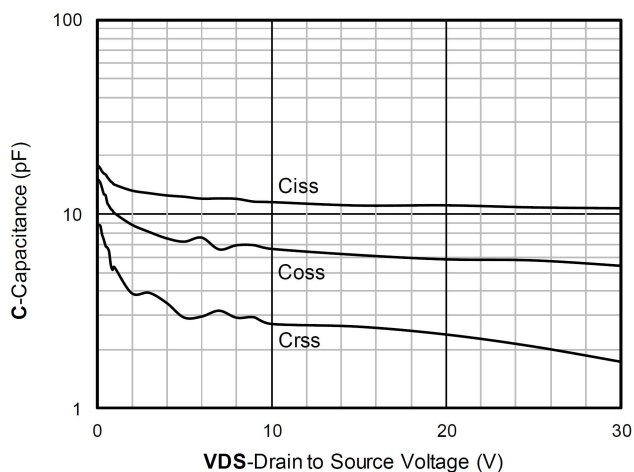
Typical Characteristics



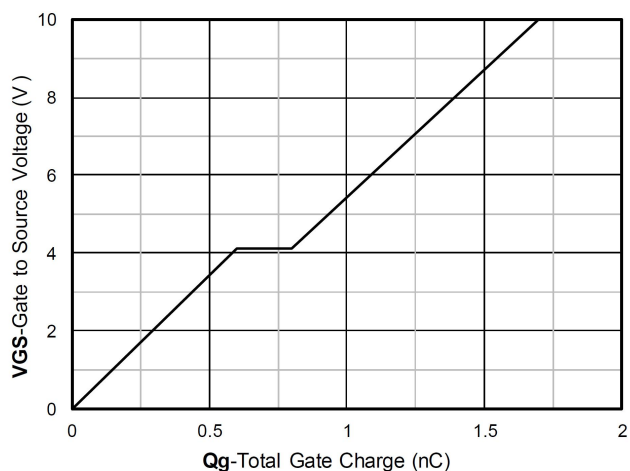
Output Characteristics



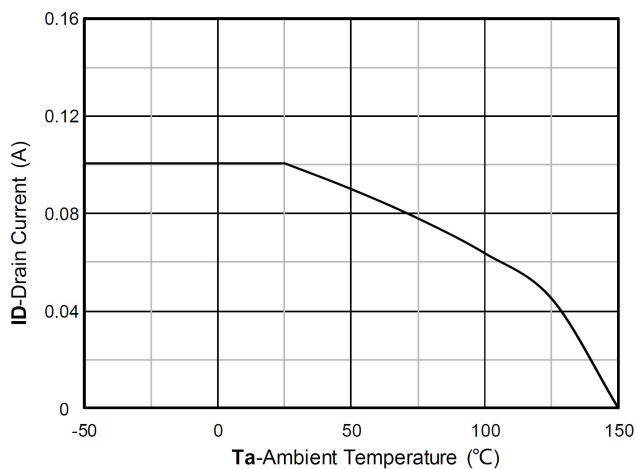
Transfer Characteristics



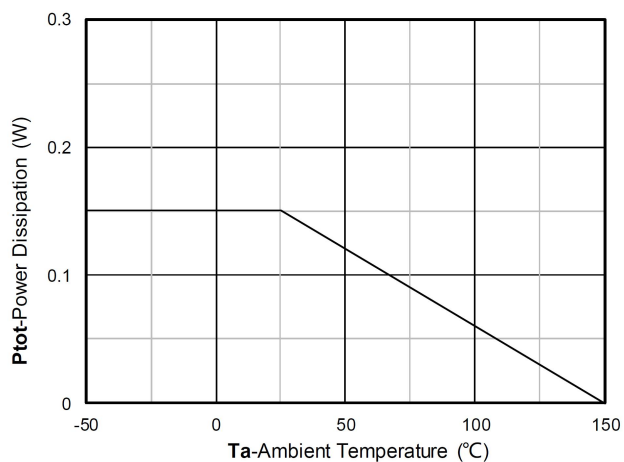
Capacitance Characteristics



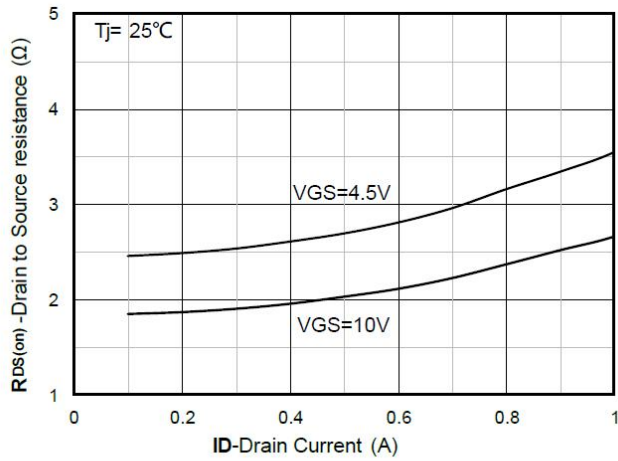
Gate Charge



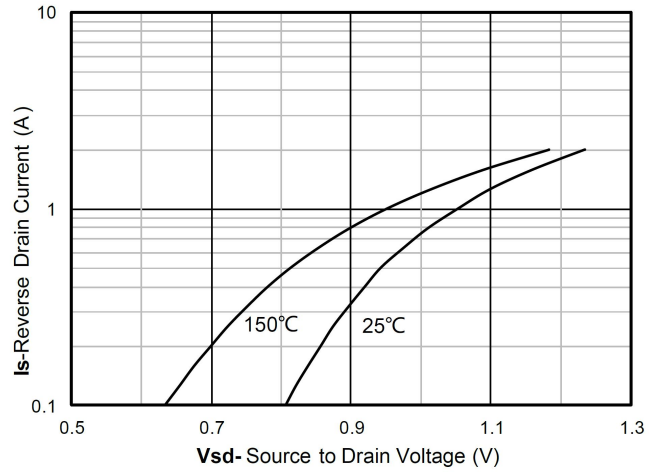
Current dissipation



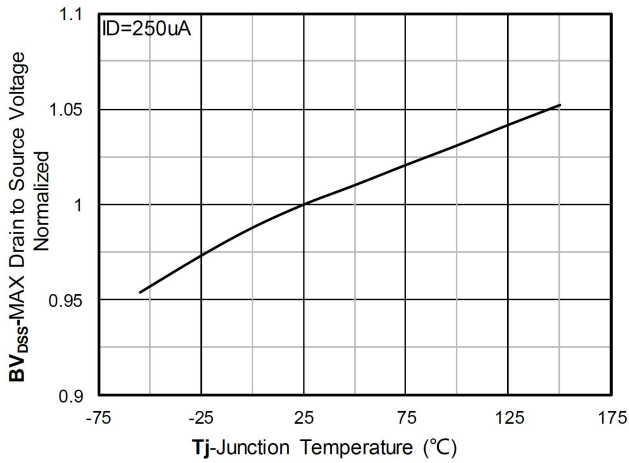
Power dissipation



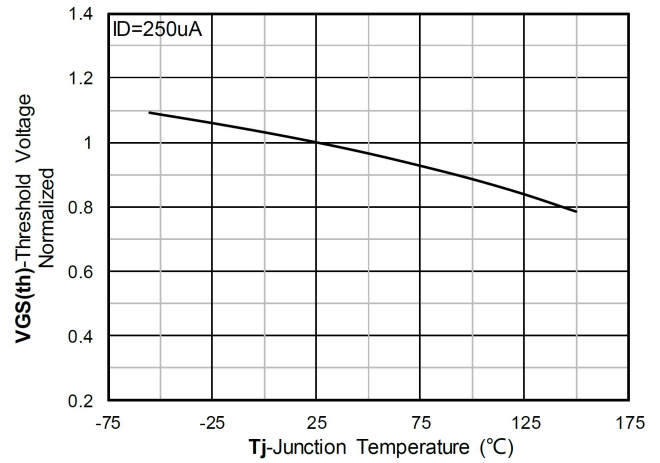
RDS(on) VS Drain Current



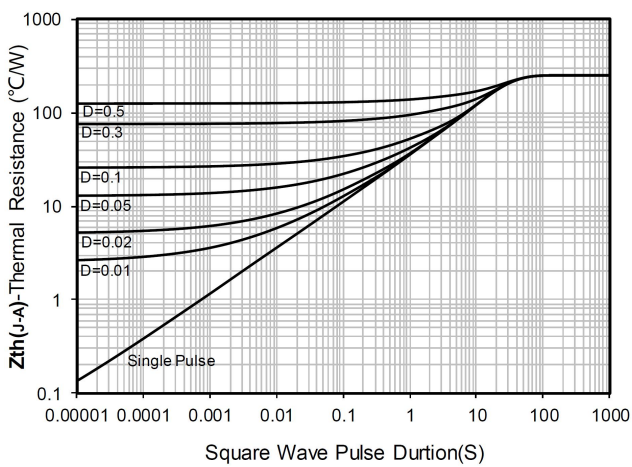
Forward characteristics of reverse diode



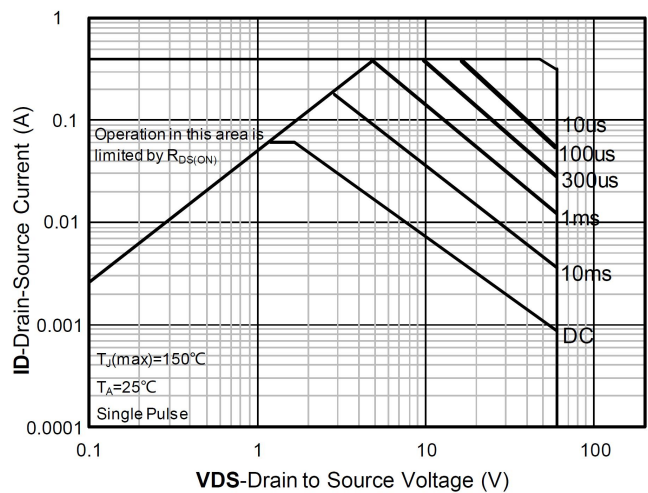
Normalized breakdown voltage



Normalized Threshold voltage

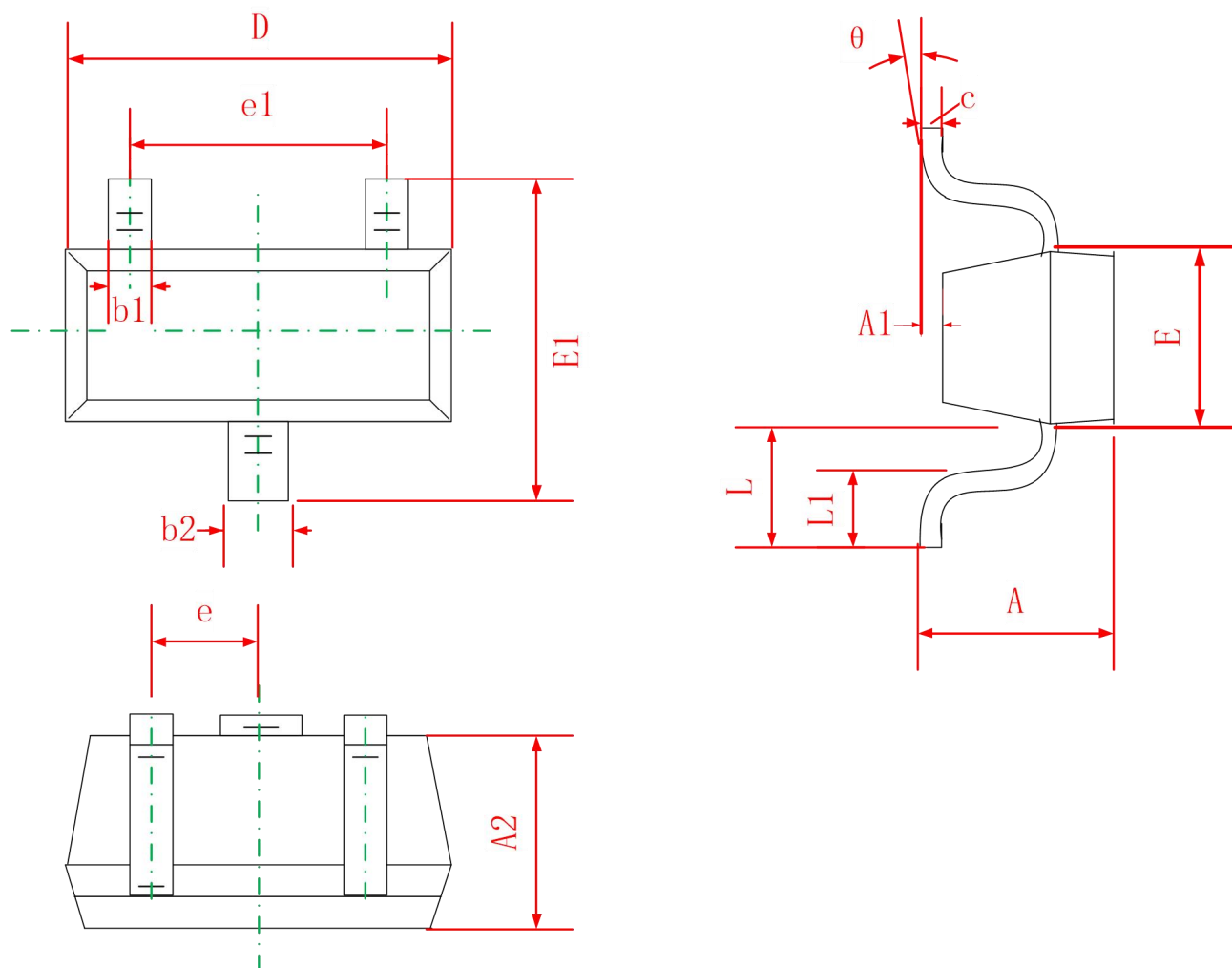


Maximum Transient Thermal Impedance



Safe Operation Area

SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°

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